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30V N-Channel NexFET™ Power MOSFET

FEATURES

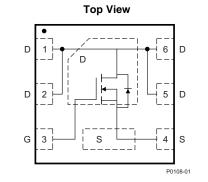
- Optimized for 5V Gate Drive
- Ultra Low Q_q and Q_{qd}
- Low Thermal Resistance
- Pb Free
- RoHS Compliant
- Halogen Free
- SON 2-mm × 2-mm Plastic Package

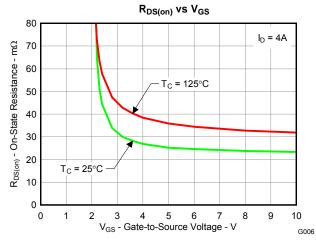
APPLICATIONS

- DC-DC Converters
- Battery and Load Management Applications

DESCRIPTION

The NexFET power MOSFET has been designed to minimize losses in power conversion applications and optimized for 5V gate drive applications. The 2-mm \times 2-mm SON offers excellent thermal performance for the size of the package.





PRODUCT SUMMARY

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V _{DS}	Drain to Source Voltage	30		V
Qg	Gate Charge Total (4.5V)	2.1		nC
Q _{gd}	Gate Charge Gate to Drain	0.4		nC
		$V_{GS} = 3V$	31	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V$	26	mΩ
		$V_{GS} = 8V$	24	mΩ
V _{GS(th)}	Threshold Voltage	1.3		V

ORDERING INFORMATION

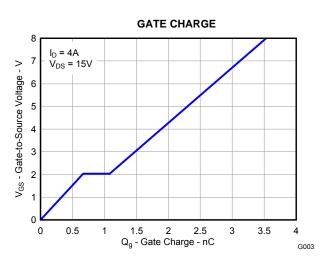
Device	Package	Media	Qty	Ship	
CSD17313Q2	SON 2-mm × 2-mm Plastic Package	13-Inch Reel	3000	Tape and Reel	

ABSOLUTE MAXIMUM RATINGS

$T_{A} = 25^{\circ}$	°C unless otherwise stated	VALUE	UNIT
V _{DS}	Drain to Source Voltage	30	V
V _{GS}	Gate to Source Voltage	+10 /8	V
	Continuous Drain Current, $T_C = 25^{\circ}C$	5	А
ID	Continuous Drain Current ⁽¹⁾	5	А
I _{DM}	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	20	А
PD	Power Dissipation	2.3	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, Single Pulse, $I_D = 19A$, $L = 0.1mH$, $R_G = 25\Omega$	18	mJ

(1) Package Limited

(2) Pulse duration ≤300µs, duty cycle ≤2%



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ΔA

CSD17313Q2





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

$(T_A = 25^{\circ}C \text{ unless otherwise stated})$

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
Static C	haracteristics	<u>.</u>			
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	30		V
I _{DSS}	Drain to Source Leakage	$V_{GS} = 0V, V_{DS} = 24V$		1	μA
I _{GSS}	Gate to Source Leakage	V _{DS} = 0V, V _{GS} = +10 / -8V		100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.9 1.3	1.8	V
		$V_{GS} = 3V$, $I_D = 4A$	31	42	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5 V, I_{D} = 4 A$	26	32	mΩ
		$V_{GS} = 8V, I_D = 4A$	24	30	mΩ
9 _{fs}	Transconductance	$V_{DS} = 15V, I_{D} = 4A$	16		S
Dynamic	Characteristics			•	
C _{iss}	Input Capacitance		260	340	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ f = 1MHz	140	180	pF
C _{rss}	Reverse Transfer Capacitance		13	17	pF
R_G	Series Gate Resistance		1.3	2.6	Ω
Qg	Gate Charge Total (4.5V)		2.1	2.7	nC
Q _{gd}	Gate Charge – Gate to Drain	V _{DS} = 15V,	0.4		nC
Q _{gs}	Gate Charge Gate to Source	$I_D = 4A$	0.7		nC
Q _{g(th)}	Gate Charge at Vth		0.3		nC
Q _{oss}	Output Charge	$V_{DS} = 13.5V, V_{GS} = 0V$	3.8		nC
t _{d(on)}	Turn On Delay Time		2.8		ns
t _r	Rise Time	V _{DS} = 15V, V _{GS} = 4.5V,	3.9		ns
t _{d(off)}	Turn Off Delay Time	$I_D = 4A, R_G = 2\Omega$	4.2		ns
t _f	Fall Time		1.3		ns
Diode C	haracteristics				
V_{SD}	Diode Forward Voltage	$I_{SD} = 4A, V_{GS} = 0V$	0.85	1	V
Q _{rr}	Reverse Recovery Charge	V_{DD} = 13.5V, I _F = 4A,	6.4		nC
t _{rr}	Reverse Recovery Time	di/dt = 300A/µs	12.9		ns

THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

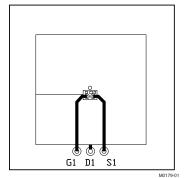
PARAMETER			TYP MA	X	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case ⁽¹⁾		7	.4	°C/W
R_{\thetaJA}	Thermal Resistance Junction to Ambient ⁽¹⁾⁽²⁾		(67	°C/W

(1) R_{θJC} is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. R_{θJC} is specified by design, whereas R_{θJA} is determined by the user's board design.
 (2) Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.

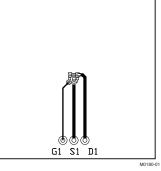


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Max $R_{\theta JA} = 67^{\circ}C/W$ when mounted on 1 inch² (6.45 cm²) of 2oz. (0.071-mm thick) Cu.



Max $R_{\theta,JA} = 228^{\circ}C/W$ when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

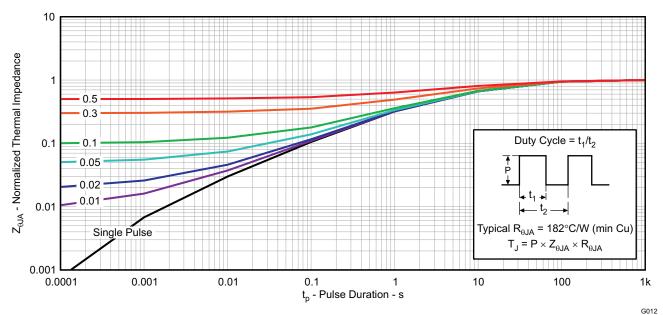


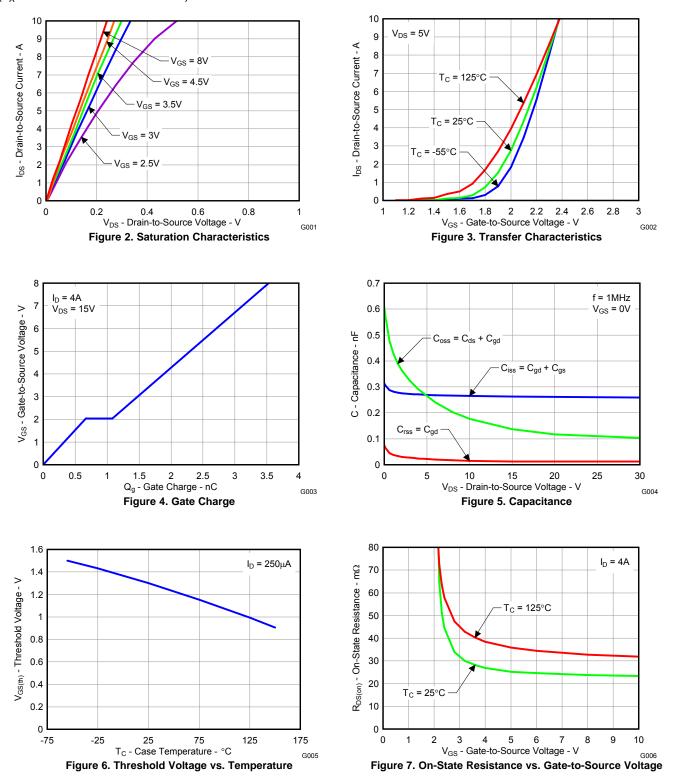
Figure 1. Transient Thermal Impedance

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$



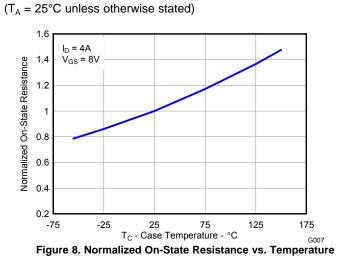




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TYPICAL MOSFET CHARACTERISTICS (continued)



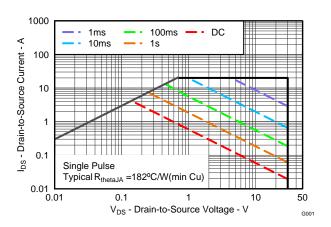
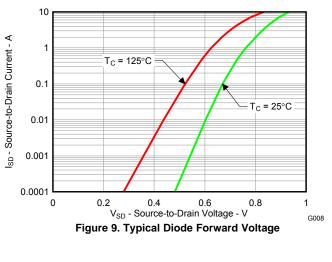


Figure 10. Maximum Safe Operating Area



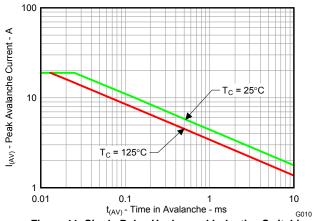
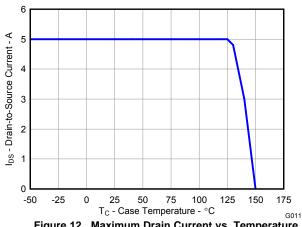


Figure 11. Single Pulse Unclamped Inductive Switching

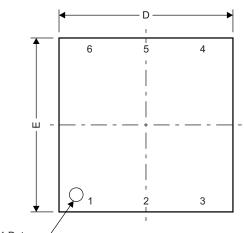


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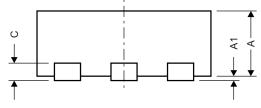
MECHANICAL DATA

Q2 Package Dimensions

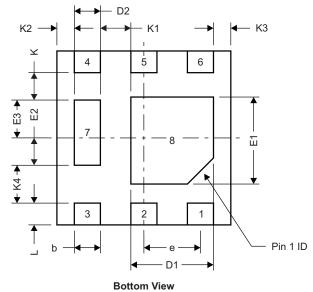








Front View



Pinout				
Source	4, 7			
Gate	3			
Drain	1, 2, 5, 6, 8			

M0175-02

DIM		MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
А	0.700	0.750	0.800	0.028	0.030	0.032	
A1	0.000		0.050	0.000		0.002	
b	0.250	0.300	0.350	0.010	0.012	0.014	
С		0.203 TYP			0.008 TYP		
D		2.000 TYP			0.080 TYP		
D1	0.900	0.950	1.000	0.036	0.038	0.040	
D2		0.300 TYP		0.012 TYP			
E	2.000 TYP				0.080 TYP		
E1	0.900	1.000	1.100	0.036	0.040	0.044	
E2		0.280 TYP			0.0112 TYP	•	
E3		0.470 TYP			0.0188 TYP		
е		0.650 BSC			0.026 TYP		
К		0.280 TYP			0.0112 TYP		
K1		0.350 TYP		0.014 TYP			
K2	0.200 TYP 0.008 TYP						
K3		0.200 TYP 0.008 TYP					
K4		0.470 TYP			0.0188 TYP		
L	0.200	0.25	0.300	0.008	0.010	0.012	

6

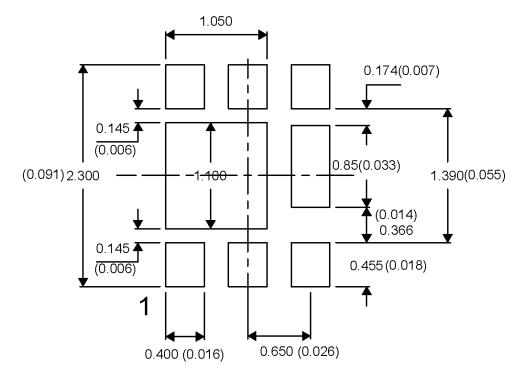


TEXAS INSTRUMENTS

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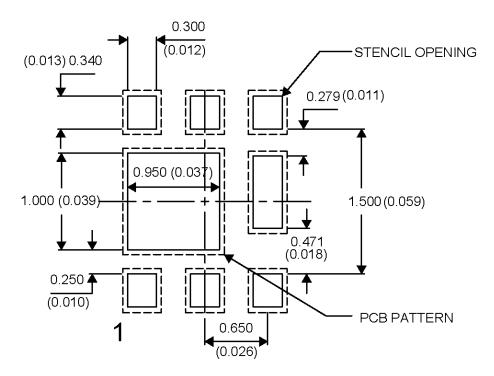
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Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing through PCB Layout Techniques.

Recommended Stencil Pattern

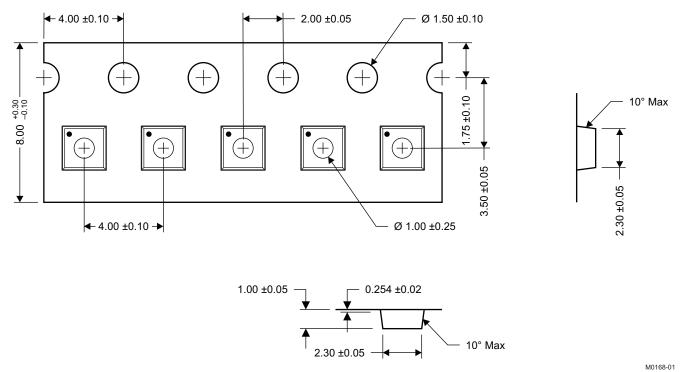


Note: All dimensions are in mm, unless otherwise specified.

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Q2 Tape and Reel Information



- Notes: 1. Measured from centerline of sprocket hole to centerline of pocket
 - 2. Cumulative tolerance of 10 sprocket holes is ±0.20
 - 3. Other material available
 - 4. Typical SR of form tape Max 10⁸ OHM/SQ
 - 5. All dimensions are in mm, unless otherwise specified.



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REVISION HISTORY

Changes from Original (March 2010) to Revision A				
Changed Q _{rr} - Reverse Recovery Charge From: 10.2 nC To: 6.4 nC				
Changes from Revision A (March 2010) to Revision B	Page			
Deleted the Package Marking Information section				
Changes from Revision B (October 2010) to Revision C	Page			
 Changed the Recommended PCB Pattern Added the Recommended Stencil Pattern 				
Changes from Revision C (January 2013) to Revision D	Page			
Changed Figure 10, Maximum Safe Operating Area	5			

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